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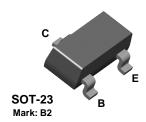
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### **BSV52**



## **NPN Switching Transistor**

This device is designed for high speed saturated switching at collector currents of 10 mA to 100 mA. Sourced from Process 21.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	12	V
V <sub>CES</sub>	Collector-Base Voltage	20	V
$V_{EBO}$	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	200	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### **Thermal Characteristics** TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		*BSV52	
P <sub>D</sub>	Total Device Dissipation	225	mW
	Derate above 25°C	1.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	556	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

(continued)

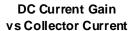
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	12		V
V <sub>(BR)CES</sub>	Collector-Base Breakdown Voltage	$I_C = 10  \mu A,  I_E = 0$	20		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 100  \mu A, I_C = 0$	5.0		V
I <sub>CBO</sub>	Collector-Cutoff Current	$V_{CB} = 10 \text{ V}, I_{E} = 0$		100	nA
		$V_{CB} = 10 \text{ V}, I_E = 0, T_A = 125^{\circ}\text{C}$		5.0	μΑ
	ACTERISTICS				
	DC Current Gain	1 10 10 1/	25		
h <sub>FE</sub>	DC Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$	40	120	
		$I_{\rm C} = 50  \text{mA},  V_{\rm CE} = 1.0  \text{V}$	25	120	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.3 mA		0.3	V
()	_	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		0.25	V
		$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$	0.7	0.85	V
		$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		1.2	V
SMALL SI	GNAL CHARACTERISTICS				
f <sub>T</sub>	Transition Frequency	$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 10 V,	400		MHz
ΙŢ	Transition Frequency	f = 100 MHz	400		IVII IZ
C <sub>cb</sub>	Collector-Base Capacitance	I <sub>E</sub> = 0, V <sub>CB</sub> = 5.0 V, f = 1.0 MHz		4.0	pF
C <sub>eb</sub>	Emitter-Base Capacitance	$I_C = 0$ , $V_{EB} = 1.0 \text{ V}$ , $f = 1.0 \text{ MHz}$		4.5	pF
	·				
SWITCHIN	NG CHARACTERISTICS				
SWITCHIN	NG CHARACTERISTICS Storage Time	$I_{B1} = I_{B2} = I_C = 10 \text{ mA}$		13	ns
		$I_{B1} = I_{B2} = I_C = 10 \text{ mA}$ $V_{CC} = 3.0 \text{ V}, I_C = 10 \text{ mA},$		13 12	ns ns
ts	Storage Time				
ts	Storage Time	$V_{CC} = 3.0 \text{ V}, I_{C} = 10 \text{ mA},$			_

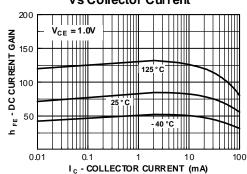
### **Spice Model**

 $NPN \ (Is=44.14f \ Xti=3 \ Eg=1.11 \ Vaf=100 \ Bf=78.32 \ Ne=1.389 \ Ise=91.95f \ Ikf=.3498 \ Xtb=1.5 \ Br=12.69m \ Nc=2 \ Isc=0 \ Ikr=0 \ Rc=.6 \ Cjc=2.83p \ Mjc=86.19m \ Vjc=.75 \ Fc=.5 \ Cje=4.5p \ Mje=.2418 \ Vje=.75 \ Tr=1.073u \ Tf=227.6p \ Itf=.3 \ Vtf=4 \ Xtf=4 \ Rb=10)$ 

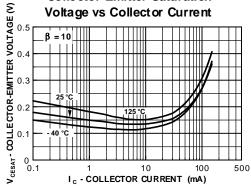
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### **Typical Characteristics**

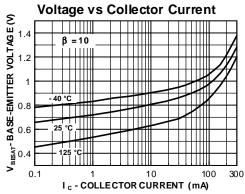




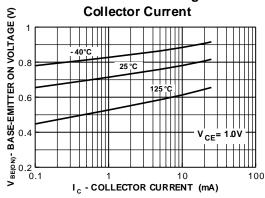
### **Collector-Emitter Saturation** Voltage vs Collector Current



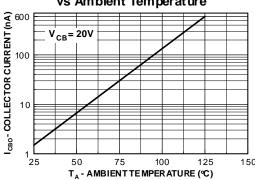
**Base-Emitter Saturation** 



Base-Emitter ON Voltage vs

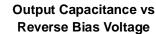


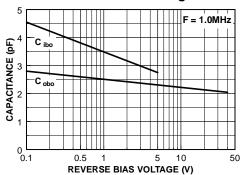
**Collector-Cutoff Current** vs Ambient Temperature



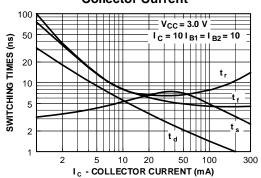
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#### Typical Characteristics (continued)

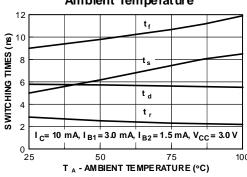




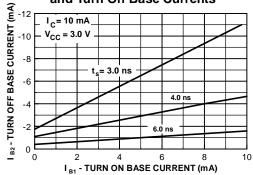
#### Switching Times vs Collector Current



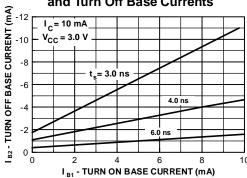
Switching Times vs Ambient Temperature



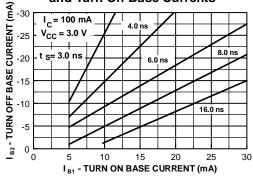
Storage Time vs Turn On and Turn Off Base Currents



Storage Time vs Turn On and Turn Off Base Currents

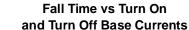


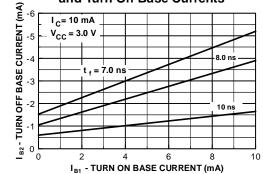
Storage Time vs Turn On and Turn Off Base Currents



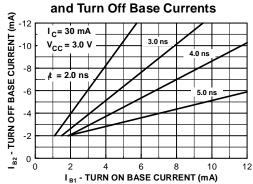
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### Typical Characteristics (continued)

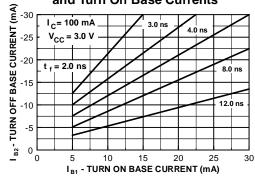




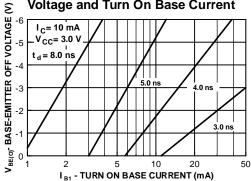
## Fall Time vs Turn On



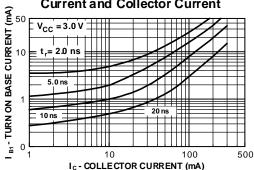
Fall Time vs Turn On and Turn Off Base Currents



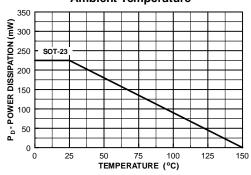
Delay Time vs Base-Emitter OFF Voltage and Turn On Base Current



Rise Time vs. Turn On Base Current and Collector Current



Power Dissipation vs Ambient Temperature



(continued)

### **Test Circuits**

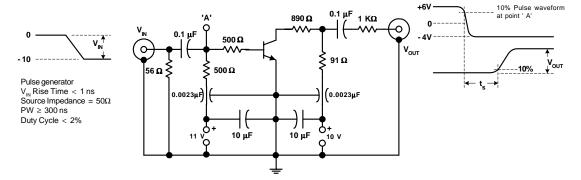


FIGURE 1: Charge Storage Time Measurement Circuit

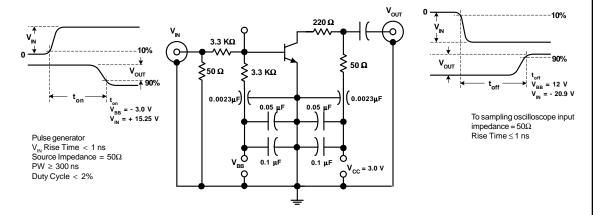


FIGURE 2:  $\mathbf{t}_{\text{ON}}, \mathbf{t}_{\text{OFF}}$  Measurement Circuit

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